



**U.S. Department of Energy
Advanced Research Projects Agency – Energy**

**Announcement of
Teaming Partner List
for
Wide Bandgap Power Semiconductor Devices
DE-FOA-0000941 (SBIR/STTR) and DE-FOA-0000942**

In June 2013, the Advanced Research Projects Agency - Energy (ARPA-E) intends to issue new Funding Opportunity Announcements (FOAs) related to wide bandgap power semiconductor devices. The objective of the FOAs will be to identify transformational concepts in wide band gap (WBG) device fabrication and device architectures that could enable the development of high voltage (1200V+), high current (100A) single die power semiconductor devices that, upon reaching scale, have the potential to reach functional cost parity with silicon power transistors while also offering breakthrough relative performance (low losses, high switching frequencies, and high temperature operation).

ARPA-E strongly encourages outstanding scientists and engineers from different organizations, scientific disciplines, and technology sectors to form new project teams. Interdisciplinary and cross-sectoral collaboration spanning organizational boundaries enables and accelerates the achievement of scientific and technological outcomes that were previously viewed as extremely difficult, if not impossible.

ARPA-E is issuing this Announcement to facilitate the formation of new project teams. Specifically, ARPA-E intends to publish a list of potential teaming partners for the FOAs on ARPA-E eXCHANGE (<http://arpa-e-foa.energy.gov>), ARPA-E's online application portal, in June 2013.

Any organization that would like to be included in this list should complete all required fields in the following link: <https://arpa-e-foa.energy.gov/Applicantprofile.aspx>. Required information includes: Organization Name, Contact Name, Contact Address, Contact Email, Contact Phone, Organization Type, Focus Area, and Brief Description of Capabilities. ARPA-E is particularly interested in receiving responses from organizations with expertise in the following Focus Areas: wide bandgap semiconductors (including GaAs, GaN, SiC, ZnO, AlN, Diamond), power semiconductor process development and fabrication, substrate fabrication, epitaxial growth, epitaxial lift-off process development, power semiconductor device design, analytical and testing services, compound semiconductor doping, implantation, annealing, defects, two-dimensional electron gas (2DEG) devices, dielectric/semiconductor interfaces, MOSFETs, IGBTs, BJTs, HEMTs, device packaging, and power electronic circuits.

By submitting a response to this Announcement, you consent to the publication of the above-referenced information. By enabling and publishing the Teaming List, the Federal Government does not endorse or otherwise evaluate the qualifications of the entities that self-identify themselves for placement on the Teaming List. The Federal Government will not pay for the provision of any information, nor will it



compensate any respondents for the development of such information. Responses submitted to other email addresses or by other means will not be reviewed or considered.

This Announcement does not constitute a FOA. Applicants must refer to the final FOAs, to be issued in June 2013 for instructions on submitting an application and for the terms and conditions of funding. ARPA-E will not review or consider noncompliant and/or nonresponsive applications.